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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 117577		APPLICATION NO. 10/689,993	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Yoshikazu KASUYA			
				FILING DATE October 22, 2003		2826	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
TT	1	6,255,166 B1	07/03/2001	Ogura et al.			
TT	2	5,408,115	04/18/1995	Chang			
TT	3	5,969,383	10/19/1999	Chang et al.			
TT	4	5,422,504	06/06/1995	Chang et al.			
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TT	8	US 2002-0100929	08/01/2002	Ebina et al.			
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TT	15	US 2003-0060011	03/27/2003	Ebina et al.			
TT	16	US 2003-0190805	10/09/2003	Inoue			
TT	17	US 2003-0186505	10/02/2003	Shibata			
TT	18	US 2003-0166321	09/04/2003	Kasuya			
TT	19	US 2003-0157767	08/21/2003	Kasuya			
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FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS SUB CLASS
TT	30	JP A 2001-156188 (with abstract and translation)	06/08/2001	Japan	
TT	31	JP A 7-161851 (with abstract and translation)	06/23/1995	Japan	
TT	32	JP B1 2978477 (with abstract and translation)	09/10/1999	Japan	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)					
TT	33	Hayashi et al. "Twin MONOS Cell with Dual Control Gates", 2000 Symposium on VLSI Technology Digest of Technical Papers			
TT	34	Chang et al. "A New SONOS Memory Using Source-Side Injection for Programming", IEEE Electron Device Letters, Vol. 19, No. 7, July 1998, pp 253-255			
TT	35	Chen et al. "A Novel Flash Memory Device with S Plit Gate Source Side Injection and ONO Charge Storage Stack (SPIN), 1997 Symposium on VLSI Technology Digest of Technical Papers, pp 63-64			
EXAMINER			DATE CONSIDERED		
We			04/05		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

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